



Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20V	35mΩ@-4.5V	-4A
	49mΩ@-2.5V	
	74mΩ@-1.8V	

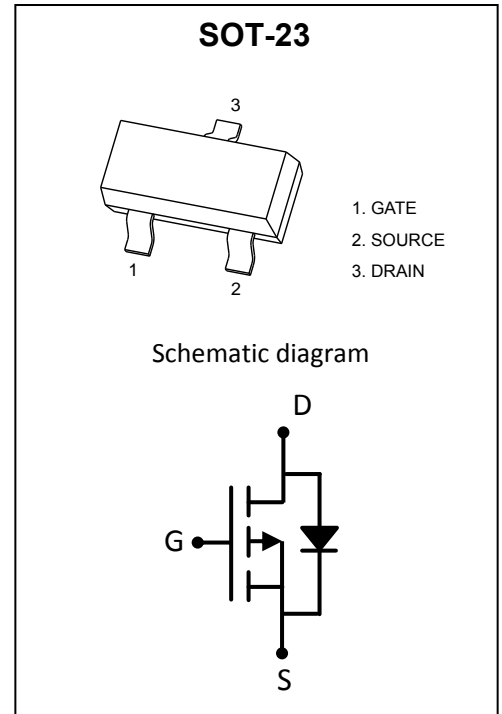
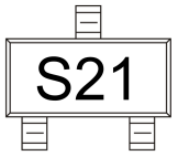
Feature

- TrenchFET Power MOSFET

Application

- PA Switch
- Load Switch

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current	I_D	-4	A
Pulsed Drain Current	I_{DM}	-12	A
Continuous Drain Current	I_S	-0.59	A
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^{\circ}\text{C}$

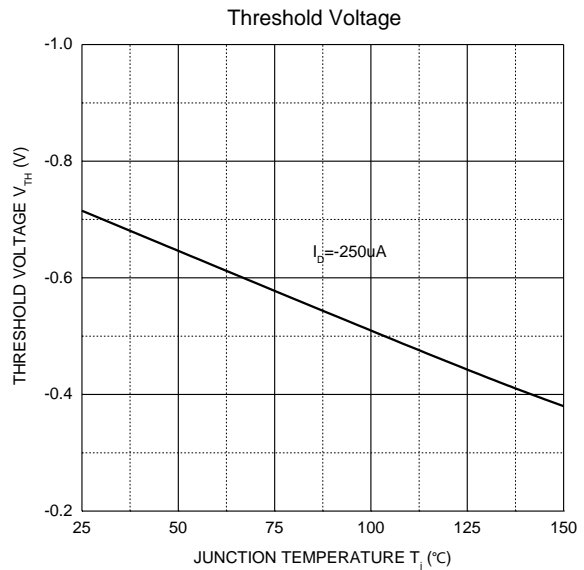
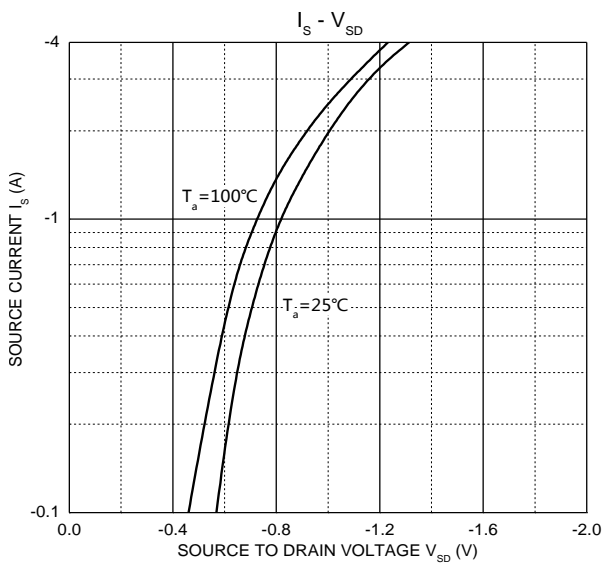
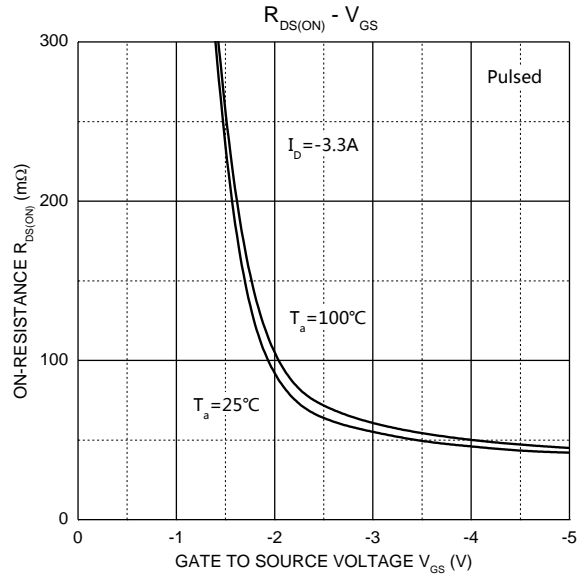
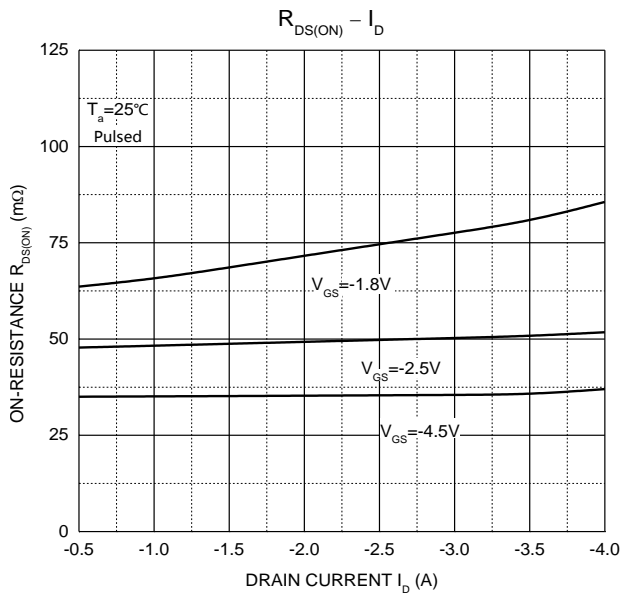
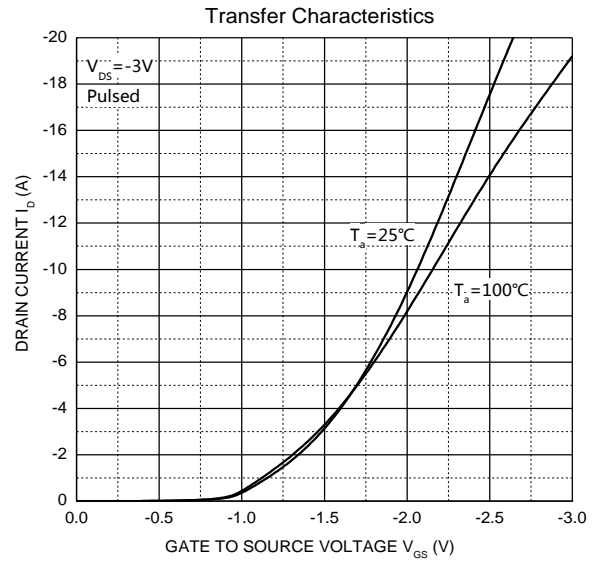
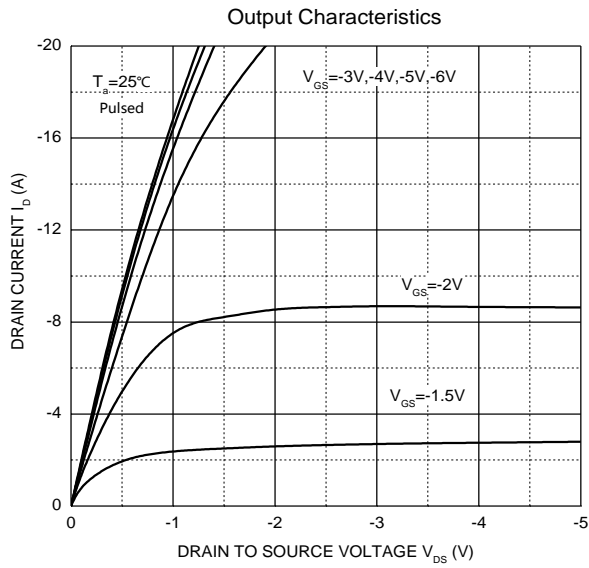
MOSFET ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20			V
Zero gate voltage drain current	I _{DSS}	V _{DS} = -16V, V _{GS} = 0V			-1	μA
Gate-body leakage current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0V			±100	nA
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.4	-0.7	-1	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -3.3A		35	45	mΩ
		V _{GS} = -2.5V, I _D = -2.8A		49	65	
		V _{GS} = -1.8V, I _D = -2.3A		74	110	
Forward tranconductance	g _{FS}	V _{DS} = -5V, I _D = -3.3A	3			S
Dynamic characteristics						
Input Capacitance ^{a,b}	C _{iss}	V _{DS} = -6V, V _{GS} = 0V, f = 1MHz		715		pF
Output Capacitance ^{a,b}	C _{oss}			170		pF
Reverse Transfer Capacitance ^{a,b}	C _{rss}			120		pF
Total Gate Charge ^a	Q _g	V _{DS} = -6V, V _{GS} = -4.5V, I _D = -3.3A			13	nC
Gate-Source Charge ^a	Q _{gs}			1.2		nC
Gate-Drain Charge ^a	Q _{gd}			1.6		nC
Switching^{a,b}						
Turn-on delay time	t _{d(on)}	V _{GEN} = -4.5V, V _{DD} = -6V, I _D = -1.0A, R _G = 6Ω, R _L = 6Ω			25	ns
Turn-on rise time	t _r				55	ns
Turn-off delay time	t _{d(off)}				90	ns
Turn-off fall time	t _f				60	ns
Source-Drain Diode characteristics						
Diode Forward voltage	V _{DS}	V _{GS} = 0V, I _S = -1.6A			-1.2	V

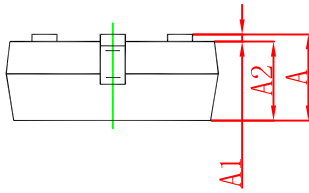
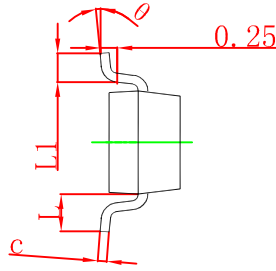
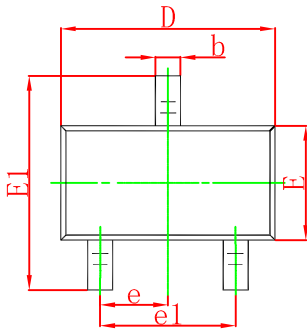
Notes:

1. Pulse test; pulse width ≤ 300μs, duty cycle ≤ 2%.
2. These parameters have no way to verify.

Typical Electrical and Thermal Characteristics



SOT-23 Package Information

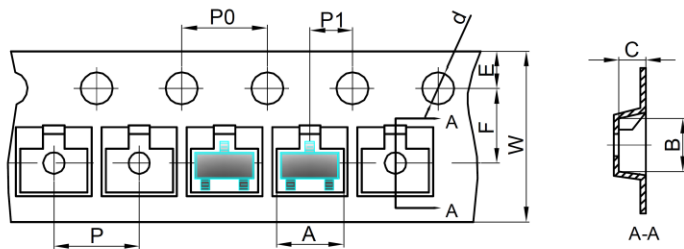


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Tape and Reel

SOT-23 Tape and reel

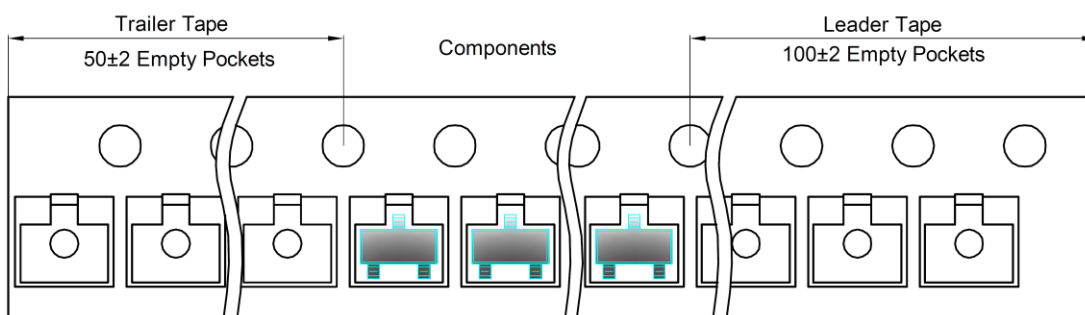
SOT-23 Embossed Carrier Tape



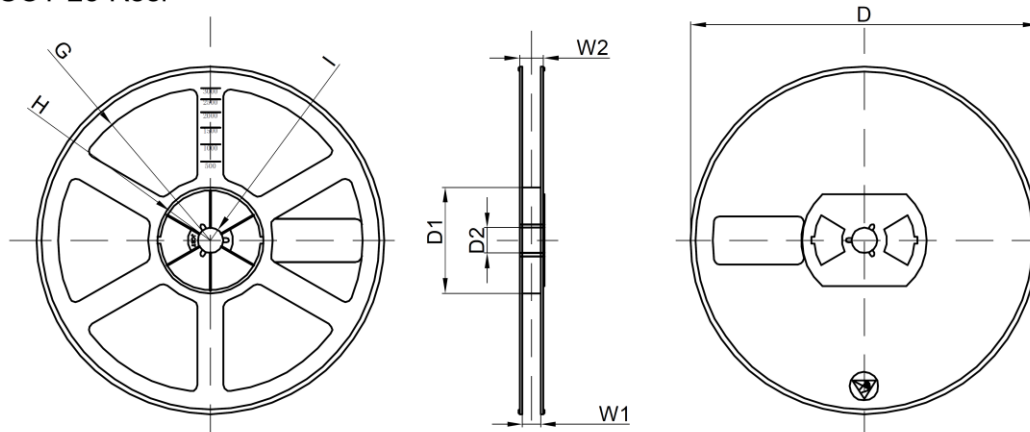
Dimensions are in millimeter

Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter

Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)